

MEMORY IP

SRAM and TCAM IP

Differentiated Features

Remarkable Features of Renesas SRAM and TCAM IP.

- Small area
 - By optimizing the peripheral circuit of memory, particularly small area is realized.
- Low power
 - Support low leak retention mode (Resume Standby) and power off mode (Shut down).
- IDM-oriented design quality
 - Many product proven.

SRAM and TCAM IP Portfolio

Foundry	Node	Cell Type	Port Type							
			1WR	2CLK		1CLK			TCAM	1WR 1.8-3.3V
				1W1R	2WR	1W1R	2WR	2W2R		
TSMC	40LP	-	✓	✓	✓					✓
	28HPL	-	✓		✓	✓				
	28 HPC	LL	✓	✓	✓	✓			*2	
		GL								✓
	28 HPC+	ULL	✓	✓	✓	✓	✓	✓	*2	✓
		GL	✓	✓	✓	✓	✓	✓	*2	✓
	16FF+	LL	✓	✓	✓	✓				
	16FFC	LL	✓	✓	✓	✓			✓	
	12FFC	LL	✓	✓	✓	✓			✓	
7FF	-	✓	✓					*1		
Samsung	7LPP	LPP	*2	*2	*2				*2	

Note: ▪ IP under development which has not been listed may also be available, so please contact us.

- 1WR -> 1 write/read port(single port) SRAM
- 1W1R -> 1write port and 1 read port(2port) SRAM
- 2WR -> 2 write/read ports(dual port) SRAM
- 1WR 1.8-3.3V -> 1 write/read port(single port) SRAM using thick gate transistor.

*1) under development (will be arrival on June 2021)

*2) under development (release schedule is TBD)

These IPs are contract design IP. Please contact for detail.

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